

Jinyu Ni

List of Publications by Year in descending order

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8
papers

185
citations

1683934

5
h-index

1872570

6
g-index

8
all docs

8
docs citations

8
times ranked

318
citing authors

#	ARTICLE	IF	CITATIONS
1	Improved electrical properties of the two-dimensional electron gas in AlGaN/GaN heterostructures using high temperature AlN interlayers. Science China Technological Sciences, 2010, 53, 1567-1571.	2.0	4
2	Improvement of electrical properties of AlGaN/GaN heterostructures using multiple high-temperature AlN interlayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1934-1937.	0.8	0
3	Effect of high temperature AlN interlayer on the performance of AlGaN/GaN properties. , 2009, , .		1
4	Study of GaN MOS-HEMT using ultrathin Al ₂ O ₃ dielectric grown by atomic layer deposition. Science in China Series D: Earth Sciences, 2009, 52, 2762-2766.	0.9	18
5	Effect of reactor pressure on the growth rate and structural properties of GaN films. Science Bulletin, 2009, 54, 2595-2598.	4.3	6
6	Development and characteristic analysis of enhancement-mode recessed-gate AlGaN/GaN HEMT. Science in China Series D: Earth Sciences, 2008, 51, 784-789.	0.9	5
7	The mobility of two-dimensional electron gas in AlGaN/GaN heterostructures with varied Al content. Science in China Series F: Information Sciences, 2008, 51, 780-789.	1.1	26
8	AlGaN/GaN MOS-HEMT With HfO_2 Dielectric and Al_2O_3 Interfacial Passivation Layer Grown by Atomic Layer Deposition. IEEE Electron Device Letters, 2008, 29, 838-840.	2.2	125